

PCN Number:	20171220001		PCN Date:	Jan. 5, 2018						
Title:	Roadster family Leadframe change to roughened									
Customer Contact:	PCN Manager		Dept:	Quality Services						
Proposed 1st Ship Date:	July 5, 2018	Estimated Sample Availability:	Date provided at sample request							
Change Type:										
<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Design	<input type="checkbox"/>	Wafer Bump Site					
<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Data Sheet	<input type="checkbox"/>	Wafer Bump Material					
<input checked="" type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change	<input type="checkbox"/>	Wafer Bump Process					
<input type="checkbox"/>	Mechanical Specification	<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Wafer Fab Site					
<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process	<input type="checkbox"/>	Wafer Fab Materials					
		<input type="checkbox"/>		<input type="checkbox"/>	Wafer Fab Process					
PCN Details										
Description of Change:										
<p>Texas Instruments Incorporated is announcing the qualification of a new Leadframe for the Roadster family of devices. The change is from non-roughened Leadframe to single-side roughened leadframe.</p> <table border="1" style="margin-left: auto; margin-right: auto;"> <thead> <tr> <th>Material</th> <th>Current</th> <th>New</th> </tr> </thead> <tbody> <tr> <td>Leadframe</td> <td>#4221093-0001 non-roughened</td> <td>#4221093-0002 single-side roughened</td> </tr> </tbody> </table>					Material	Current	New	Leadframe	#4221093-0001 non-roughened	#4221093-0002 single-side roughened
Material	Current	New								
Leadframe	#4221093-0001 non-roughened	#4221093-0002 single-side roughened								
Reason for Change:										
Improvement of reliability.										
Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):										
None.										
Changes to product identification resulting from this PCN:										
None.										
Product Affected:										
LM536023QPWPRQ1	LM536033QPWPRQ1									
LM536023QPWPTQ1	LM536033QPWPTQ1									
LM536025QPWPRQ1	LM536035QPWPRQ1									
LM536025QPWPTQ1	LM536035QPWPTQ1									
LM53602AQPWPRQ1	LM53603AQPWPRQ1									
LM53602AQPWPTQ1	LM53603AQPWPTQ1									



Automotive New Product Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

LM53603BQPWPTDN - die revision C2

Approved 24-Aug-2017

Updated 11/06/2017-Added QBS Data

Product Attributes

Attributes	Qual Device: <u>LM53603BQPWPDN</u>	QBS Product Reference: <u>LM53603BQPWPDN</u>	QBS Product Reference: <u>LM53603QPWPO1</u>	QBS Process Reference: <u>LM43603QPWPO1</u>
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range	-40 to +125 C	-40 to +125 C	-40 to +125 C	-40 to +125 C
Product Function	Power Management	Power Management	Power Management	Power Management
Wafer Fab Supplier	DM5-DALLAS	DM5-DALLAS	DM5-DALLAS	DMOS5
Die Revision	C2	C1	B3	C1
Assembly Site	TAI / TITL	TAI / TITL	TAI / TITL	TAI / TITL
Package Type	HTSSOP	HTSSOP	HTSSOP	HTSSOP
Package Designator	PWP	PWP	PWP	PWP
Ball/Lead Count	16	16	16	16

- QBS: Qual By Similarity

- Qual Device LM53603BQPWPDN is qualified at LEVEL3-260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: <u>LM53603BQPWPDN</u>	QBS Product Reference: <u>LM53603BQPWPDN</u>	QBS Product Reference: <u>LM53603QPWPO1</u>	QBS Process Reference: <u>LM43603QPWPO1</u>
Test Group A – Accelerated Environment Stress Tests										
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	Level 3-260C	-	3/693/0	-	3/969/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 110C/85%RH	264 Hours	-	-	-	3/231/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	-	3/231/2 [a]	-	-
AC	A3	JEDEC JESD22-A102	3	77	Autoclave 121C	96 Hours	-	3/231/0	-	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	-	3/231/0	-	2/154/0
TC-BP	A4	MIL-STD883 Method 2011	3	30	Post Temp. Cycle Bond Pull	Cpk >1.67	-	1/5/0	-	1/10/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle	10000 Cycles	-	-	-	3/231/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle, -40/125C	1000 Cycles	-	1/45/0	-	1/45/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp. Storage Bake, 150C	1000 Hours	-	1/77/0	-	-
Test Group B – Accelerated Lifetime Simulation Tests										
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 150C	408 Hours	1/77/0	-	1/77/0	3/231/1 [b]
ELFR	B2	AEC Q100-	3	800	Early Life Failure Rate,	24 Hours	-	-	-	3/2400/4 [b]

		008			150C					
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	150C x 1000 hours	-	-	-	3/231/0
Test Group C – Package Assembly Integrity Tests										
WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	-	Pass	-	-
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	-	Pass	-	-
SD	C3	JEDEC JESD22-B102	1	15	Solderability (>95% Lead Coverage)	Pb-Free	-	Pass	-	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Cpk>1.33 Ppk>1.67)	--	-	Pass	-	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	--	-	Pass	-	-
Test Group D – Die Fabrication Reliability Tests										
EM	D1	JESD61	-	-	Electro migration	--	Completed Per Process Technology Requirements	-	-	-
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	--	Completed Per Process Technology Requirements	-	-	-
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	--	Completed Per Process Technology Requirements	-	-	-
NBTI	D4	-	-	-	Negative Bias Temperature Instability	--	Completed Per Process Technology Requirements	-	-	-
SM	D5	-	-	-	Stress Migration	--	Completed Per Process Technology Requirements	-	-	-
Test Group E – Electrical Verification Tests										
HBM	E2	AEC Q100-002	1	3	ESD – HBM	2500 V	1/3/0	-	1/3/0	1/3/0
CDM	E3	AEC Q100-011	1	3	ESD - CDM	1000 V	1/3/0	-	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-up	(Per AEC Q100-004)	1/6/0	-	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, Hot, & Cold	Pass	Pass	Pass	Pass

Reject dispositioning

[a] 2 EOS failures were due to a failure in the BHAST hardware. This was discounted as not being related to the product reliability

[b] 5 failures due to inadvertent electrical overstress of an ESD protection diode between the EN & VIN pins. Root cause was incorrect HTOL hardware configuration where EN pin could be more positive than VIN during operational life test. This condition would turn on the ESD protection circuit during HTOL leading to burn out of the circuit. EN > VIN is an invalid datasheet condition.

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST & TC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C

Grade 1 (or Q): -40°C to +125°C

Grade 2 (or T): -40°C to +105°C

Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

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